

AMENDMENTS TO THE CLAIMS

Claims 1-11 (Canceled).

12. (Previously Presented) An integrated circuit comprising:
a substrate having a circuit device;
a dielectric material overlying the circuit device with a via formed in the dielectric material to the circuit device, the via exposing a sidewall in the dielectric material and a surface of the circuit device;
a barrier material substantially lining the sidewall;
a seed layer on the barrier material and substantially lining the sidewall; and
a conductive material on the seed layer and directly contacting the surface of the circuit device.
13. (Previously Presented) The integrated circuit of claim 12, wherein the circuit device comprises an interconnection line.
14. (Previously Presented) The integrated circuit of claim 12, wherein the conductive material is copper.
15. (Currently Amended) The integrated circuit of claim 12, wherein the seed layer is a mask layer that ~~is not over~~does not completely cover the surface of the circuit device, and the barrier layer comprises an etch characteristic such that the barrier material can be selectively etched in the presence of the mask layer.
16. (Previously Presented) An integrated circuit comprising:
a substrate having a circuit device;
a dielectric material overlying the circuit device with a via formed in the dielectric material to the circuit device, the via exposing a sidewall in the dielectric material and a surface of the circuit device;
a barrier material substantially lining the sidewall;

a seed layer on the barrier material and substantially lining the sidewall, but not on the surface of the circuit devices; and

a conductive material in the via;

wherein the seed layer and barrier material are formed so as to expose the circuit device at an end of the via.

17. (Currently Amended) The integrated circuit of claim 16, wherein the seed layer is a mask layer that ~~is not over~~does not completely cover the surface of the circuit device, and the barrier layer comprises an etch characteristic such that the barrier material can be selectively etched in the presence of the seed material.